04/14/2006 AP20 Rec'C NOTETO 14 APR 200

S/N: TBA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: TO BE ASSIGNED Confirmation No.: TO BE ASSIGNED

Applicant: Masato YAMADA et al. Art Unit: TO BE ASSIGNED

Filed: April 14, 2006 Examiner: TO BE ASSIGNED

Docket No: SUG-190-PCT Customer No: 28892

For: Light Emitting Device and Method of Fabricating the Same

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§ 1.56, 1.97, and 1.98

US Patent & Trademark Office Customer Service Window Randolph Building 401 Dulany Street Alexandria, VA 22314

Sir:

In compliance with the dictates of 37 C.F.R. §§ 1.56, 1.97, and 1.98, Applicant hereby submits an Information Disclosure Statement. Applicant hereby reports the issuance of a Search Report in the corresponding application. A copy of that Search Report and the references cited therein, together with PTO Form 1449 listing each of the references is attached hereto.

It is respectfully requested that the Examiner consider each of these references and indicate such consideration by enclosing an appropriately initialled copy of the enclosed form PTO-1449 with the next communication from the Patent Office.

Respectfully submitted,

Ronalder. Snider Attorney of Record Reg. No. 24,962

Date: April 14, 2006

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INFORMATION DISCLOSURE STATEMENT - PTO FORM 1449

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Foreign Patent Document Number	Name of Patentee or App of Cited Document	of Ci	of Publication ted Document M-DD-YYYY	T**
	JP 2002-237617 w/ English Abstract	Tokyo Shibaura Electric	c Co O	8-23-2002	
	JP 10-65210 w/ English Abstract	Mitsubishi Cable Ind I	Ltd 0	3-06-1998	
	JP 6-296040 w/ English Abstract	Sharp KK	1	0-21-1994	х
	JP 4-354382 w/ English Abstract	Shinetsu Handotai K	K 1	2-08-1992	-
	OTHER PRIOR AR	RT - NON PATENT LITERAT	TURE DOCUM	ENTS	
Examiners Initials*	Include Author (CAPITAL LETTERS), title of article, book, magazine, etc. date, page(s), volume-issue number(s), publisher, city and/or country where published				T**
	KISH, F.A., et al., "Very high-efficiency semiconductor wafer-bonded transparent-substrate(Al _x Ga _{1-x}) _{0.5} ln _{0.5} P/GaP light-emitting diodes," <u>Applied Physics Letters</u> , 1964, Abstract (vol. 64, pages 2839-2841)				
	HUANG, K.H. et al., "Twofold efficiency improvement in high performance AlGalnP light-emitting diodes in 555-620 nm spectral region using a thick GaP window layer," <u>Applied Physics Letters</u> , 1992, Abstract (Vol. 61, pp. 1045-1047)				
Examiner Signature			Date Considered		

^{*}Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

^{**}Applicant is to place a check mark here if English language translation is attached